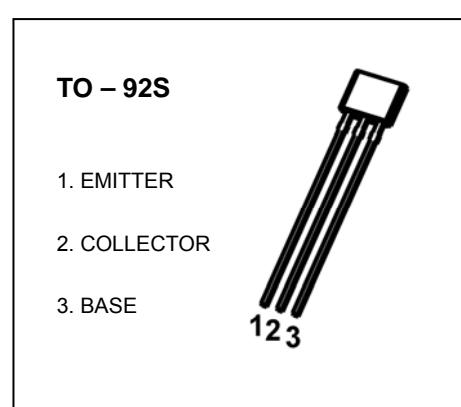




TO-92S Plastic-Encapsulate Transistors

2SA1317 TRANSISTOR (PNP)**FEATURES**

- Large Current Capacity and Wide ASO

**MAXIMUM RATINGS (T_a=25°C unless otherwise noted)**

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage	-60	V
V _{CEO}	Collector-Emitter Voltage	-50	V
V _{EBO}	Emitter-Base Voltage	-6	V
I _c	Collector Current	-0.2	A
P _c	Collector Power Dissipation	300	mW
R _{θJA}	Thermal Resistance From Junction To Ambient	417	°C/W
T _j	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55~+150	°C

ELECTRICAL CHARACTERISTICS (T_a=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _c =-0.01mA, I _e =0	-60			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _c =-1mA, I _b =0	-50			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _e =-0.01mA, I _c =0	-6			V
Collector cut-off current	I _{CBO}	V _{CB} =-40V, I _e =0			-0.1	μA
Emitter cut-off current	I _{EBO}	V _{EB} =-5V, I _c =0			-0.1	μA
DC current gain	h _{FE(1)}	V _{CE} =-6V, I _c =-1mA	100		560	
	h _{FE(2)}	V _{CE} =-6V, I _c =-0.1mA	70			
Collector-emitter saturation voltage	V _{CE(sat)}	I _c =-100mA, I _b =-10mA			-0.3	V
Base-emitter saturation voltage	V _{BE (sat)}	I _c =-100mA, I _b =-10mA			-1	V
Collector output capacitance	C _{ob}	V _{CB} =-6V, I _e =0, f=1MHz		4		pF
Transition frequency	f _T	V _{CE} =-6V, I _c =-10mA		200		MHz

CLASSIFICATION OF h_{FE(1)}

RANK	R	S	T	U
RANGE	100-200	140-280	200-400	280-560